

## AM7461P-VB Datasheet

### P-Channel 60 V (D-S) 175 °C MOSFET

#### PRODUCT SUMMARY

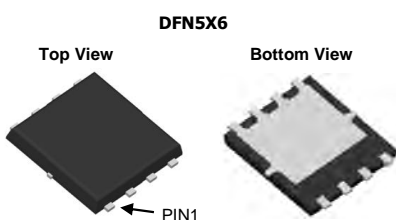
$V_{DS}$ (V)	-60
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -10$ V	0.0210
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5$ V	0.0288
$I_D$ (A)	-36
Configuration	Single
Package	DFN 5X6

#### FEATURES

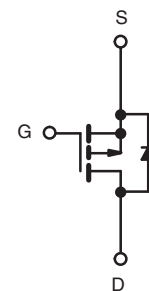
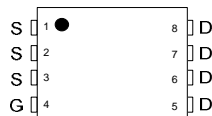
- Trench power MOSFET
- 100 %  $R_g$  and UIS tested



**RoHS**  
COMPLIAN  
HALOGEN  
**FREE**



Top View



P-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	-36	A
		-21	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	-60	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	-100	
Single Pulse Avalanche Current	$I_{AS}$	-36	mJ
Single Pulse Avalanche Energy	$E_{AS}$	64.8	
Maximum Power Dissipation <sup>b</sup>	$P_D$	68	W
		22	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260	

#### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	$R_{thJA}$	68	°C/W
Junction-to-Case (Drain)	$R_{thJC}$	2.2	

#### Notes

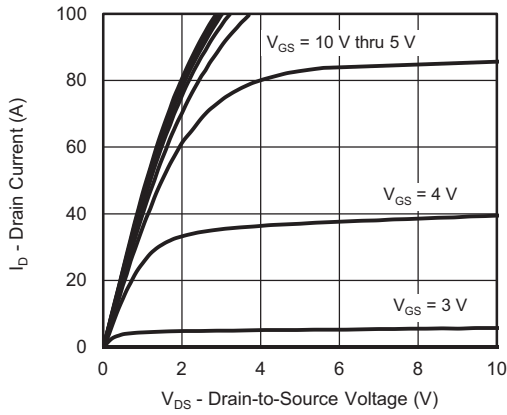
- Package limited.
- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.
- When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = -250 μA		-60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA		-1.5	-2.0	-2.5	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V	-	-	-1	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V, T <sub>J</sub> = 125 °C	-	-	-50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V, T <sub>J</sub> = 175 °C	-	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> ≥ -5 V	-30	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A	-	0.0210	-	Ω
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 125 °C	-	0.0409	-	
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 175 °C	-	0.0504	-	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -5 A	-	0.0288	-	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -10 A		-	26	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -25 V, f = 1 MHz	-	2600	3400	pF
Output Capacitance	C <sub>oss</sub>			-	310	450	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	200	275	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> = -30 V, I <sub>D</sub> = -5 A	-	65	100	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			-	9.5	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	19	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.50	1.19	1.80	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = -30 V, R <sub>L</sub> = 6 Ω I <sub>D</sub> ≅ -5 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 Ω		-	15	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			-	5	10	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	40	75	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	6	12	
Source-Drain Diode Ratings and Characteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-100	A
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = -10 A, V <sub>GS</sub> = 0 V		-	-0.80	-1.2	V

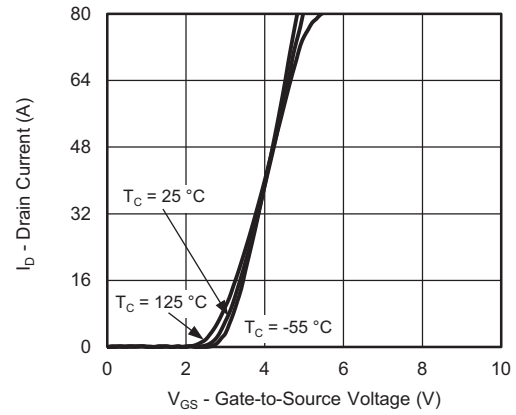
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

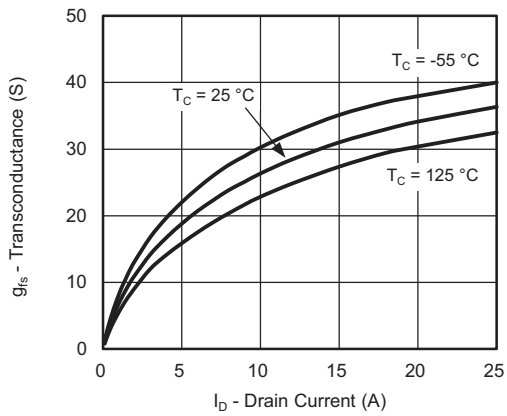
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



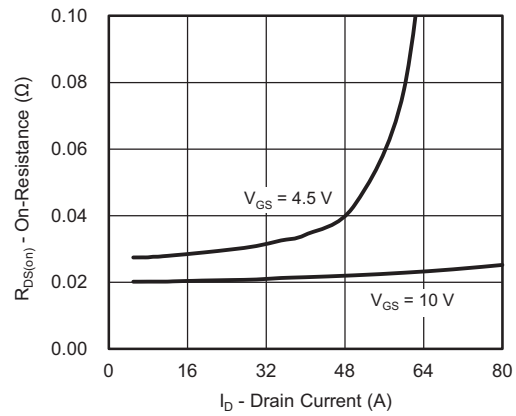
**Output Characteristics**



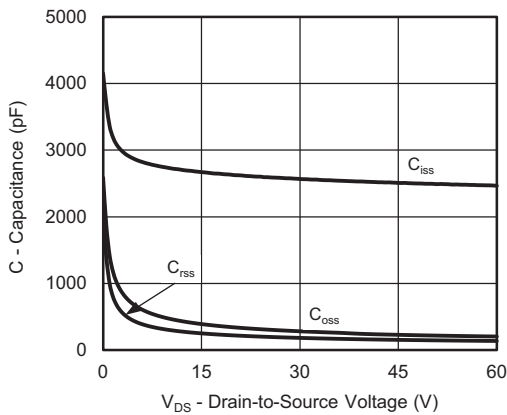
**Transfer Characteristics**



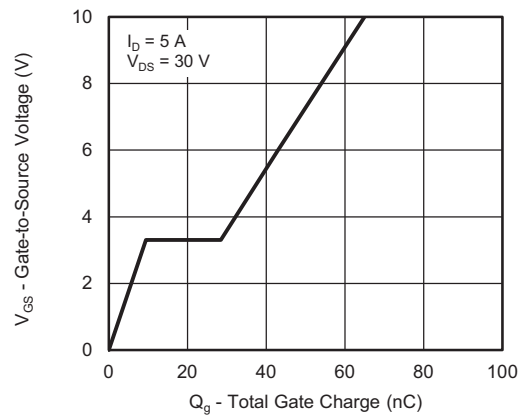
**Transconductance**



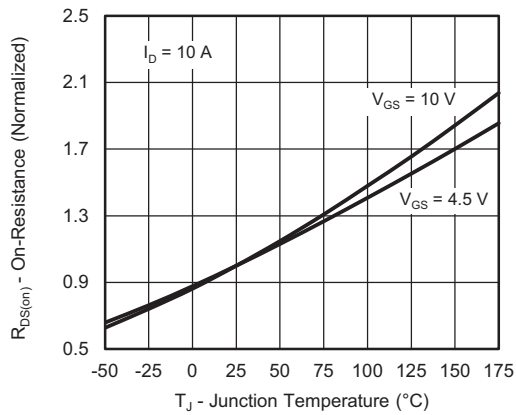
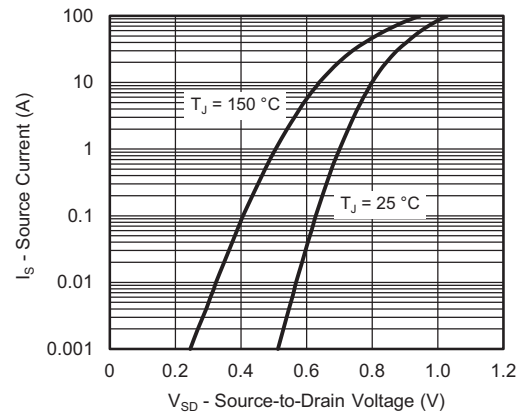
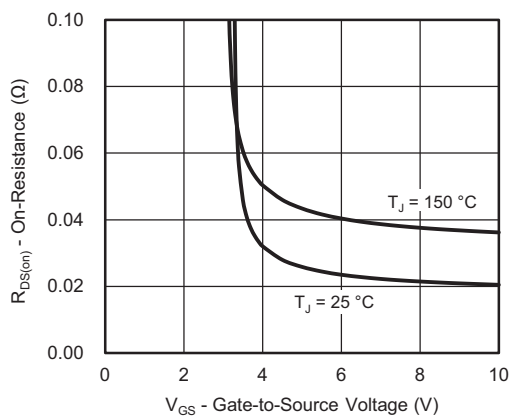
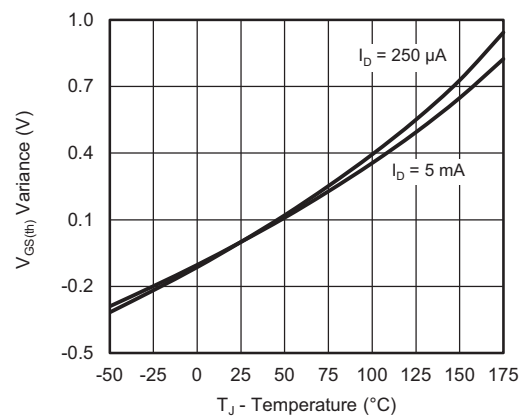
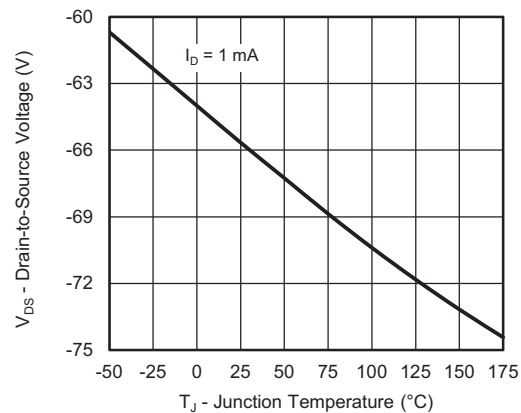
**On-Resistance vs. Drain Current**



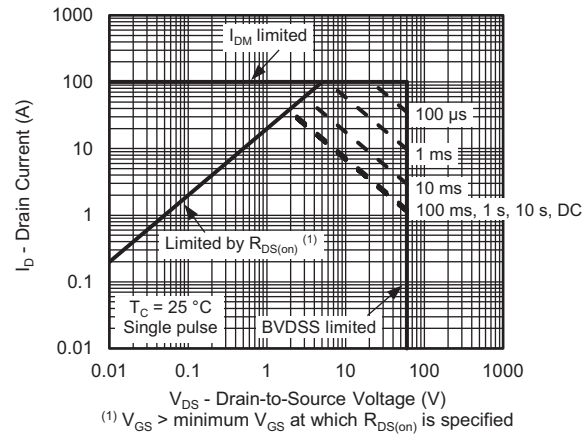
**Capacitance**



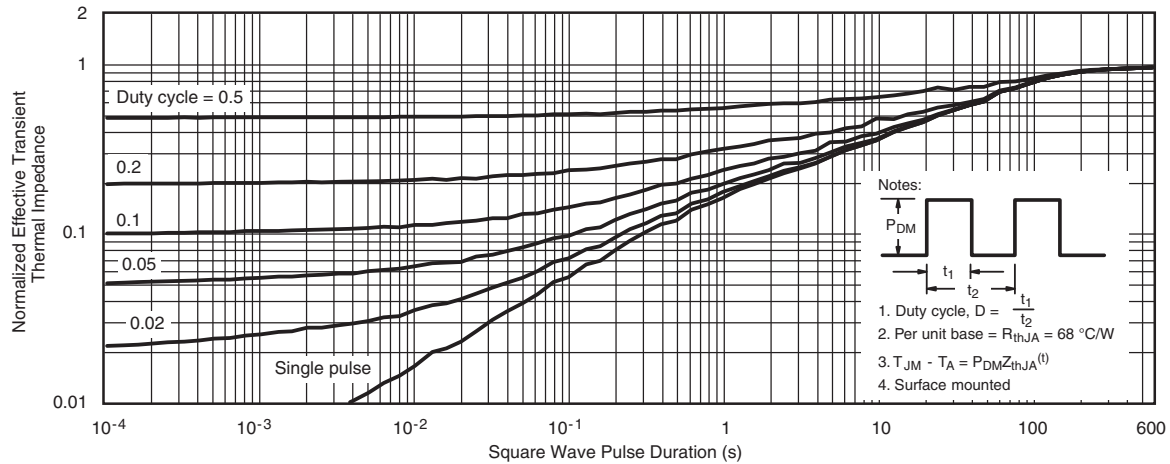
**Gate Charge**

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**On-Resistance vs. Junction Temperature**

**Source Drain Diode Forward Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

**Threshold Voltage**

**Drain-Source Breakdown vs. Junction Temperature**

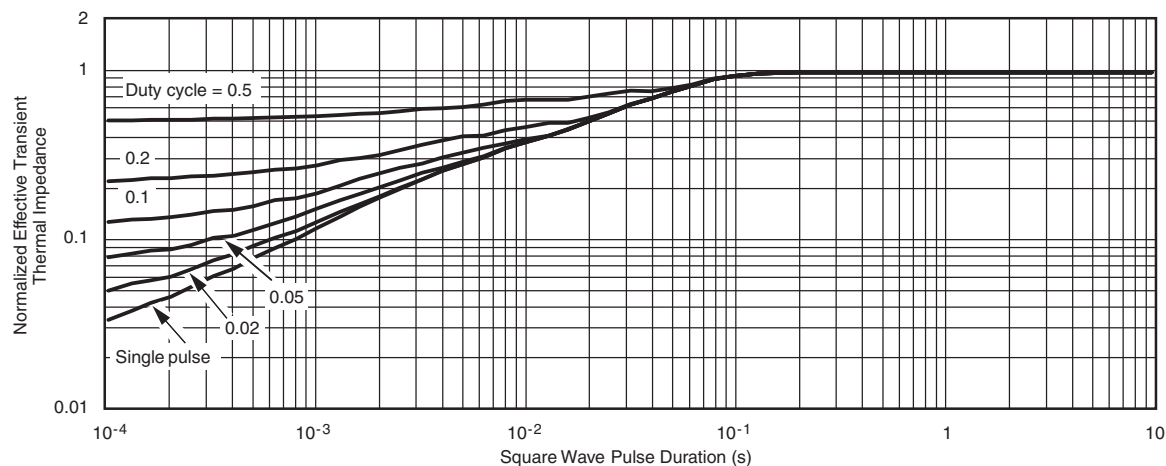
**THERMAL RATINGS** ( $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)



**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)


**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^{\circ}\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Case ( $25\text{ }^{\circ}\text{C}$ )
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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